

## STANDARD LOW COST HERMETIC MOSFET MODULES

**FEATURES:**

- High Power Density
- Low Drain to Source Resistance ( $R_{DS(on)}$ )
- Low Thermal Resistance ( $R_{qJC}$ )

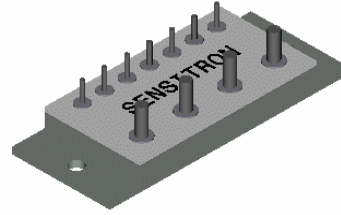
**INDUSTRIAL MOSFET PRODUCT MAP**

		$I_D$ (Amps)			
CONFIGURATION	$V_{DSS}$ (V)	25	50	100	200
Half-Bridge	60	-	-	-	LPM2M200-006 LPM2M250-006
	100	-	-	LPM2M150-010	LPM2M200-010
	300	-	-	LPM2M080-030 LPM2M120-030	-
	600	-	LPM2M040-060 LPM2M060-060	-	-
	1000	LPM2M025-100 LPM2M035-100	-	-	-
H-Bridge	60	-	-	LPM4M130-006	-
	100	-	-	LPM4M130-010	-
	300	-	-	LPM4M080-030	-
	600	-	LPM4M040-060	-	-
	1000	LPM4M024-100	-	-	-

## STANDARD LOW-COST HERMETIC MOSFET MODULES

### MOSFET Module Features:

- Sensitron low-cost hermetic package.
- Low  $R_{ds(on)}$  MOSFET devices.
- Fast reverse recovery intrinsic rectifier.
- DBC ALN substrate on copper base-plate.
- Pin-to-case voltage isolation up to 2500V.
- Rating up to 60V, 250A; 600V, 100A; 1000V, 50A.
- Half-bridge and H-bridge configurations.
- Unit Price: Starting at \$165 per 100 pcs.



### Half-Bridge Devices<sup>(1)</sup>

MOSFET CHARACTERISTICS									
PART NUMBER	$V_{DSS}$	Continuous Drain Current $I_D$ @ $T_C=25^\circ C$	Pulsed Drain Current $T_C=25^\circ C$	$R_{ds(on)}@I_D$		$C_{iss}$ Typ	$t_{rr}$ max 25°C	Maximum $P_D$ @ $T_C=25^\circ C$	$R_{\theta JC}$
	Volts			Amps	Amps				
LPM2M200-006	60	200	500	0.005	40	9	60	460	0.27
LPM2M250-006	60	250	600	0.004	60	14	60	600	0.20
LPM2M150-010	100	150	400	0.013	40	9	200	600	0.20
LPM2M200-010	100	200	500	0.009	60	14	200	900	0.13
LPM2M080-030	300	80	250	0.055	40	9	200	600	0.20
LPM2M120-030	300	120	350	0.035	60	14	200	900	0.13
LPM2M040-060	600	40	150	0.180	20	9	250	600	0.20
LPM2M060-060	600	60	200	0.120	30	14	250	900	0.13
LPM2M025-100	1000	25	75	0.55	10	9	250	600	0.20
LPM2M035-100	1000	35	120	0.37	15	14	250	900	0.13

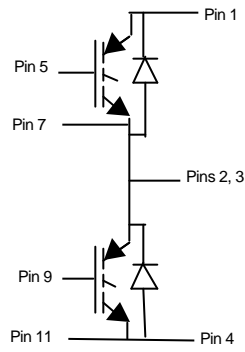
### H-Bridge Devices<sup>(1)</sup>

MOSFET CHARACTERISTICS									
PART NUMBER	$V_{DSS}$	Continuous Drain Current $I_C$ @ $T_C=25^\circ C$	Pulsed Drain Current $T_C=25^\circ C$	$R_{ds(on)}@I_D$		$C_{iss}$ Typ	$t_{rr}$ max 25°C	Maximum $P_D$ @ $T_C=25^\circ C$	$R_{\theta JC}$
	Volts			Amps	Amps				
LPM4M130-006	60	130	400	0.006	20	6	60	230	0.56
LPM4M130-010	100	130	400	0.011	20	9	200	600	0.20
LPM4M080-030	300	80	300	0.053	20	9	200	600	0.20
LPM4M040-060	600	40	120	0.180	20	9	250	900	0.20
LPM4M024-100	1000	24	70	0.55	15	9	250	600	0.20

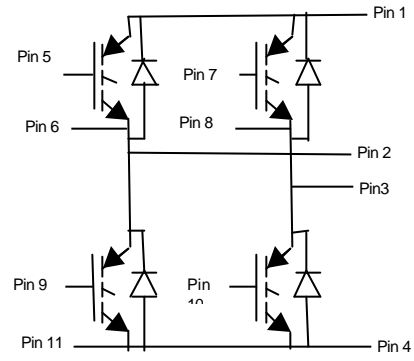
**Notes:**

- 1- Contact Sensitron for your custom requirements.

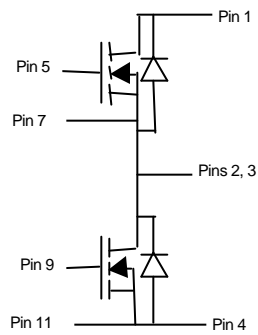
## SCHEMATIC DIAGRAMS



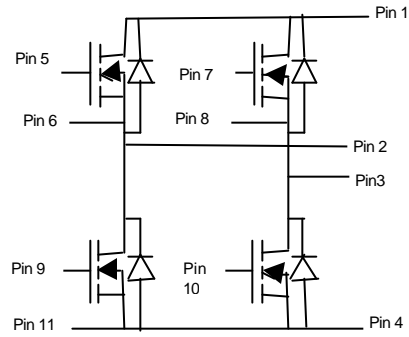
(a) Half-Bridge IGBT Device



(b) H-Bridge IGBT Device

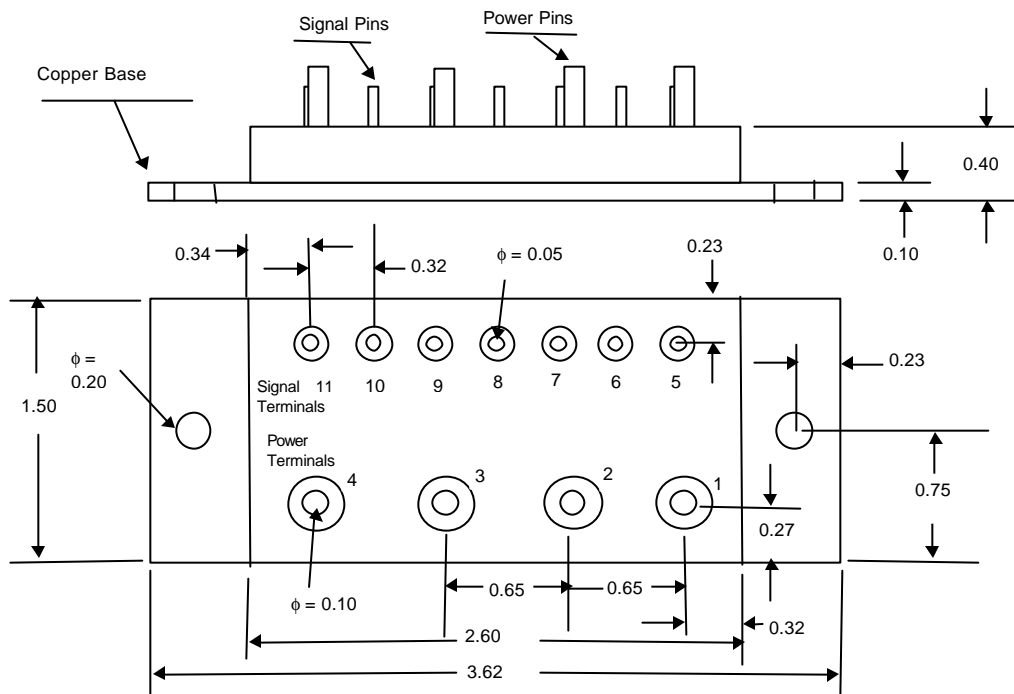


(a) Half-Bridge MOSFET Device



(b) H-Bridge MOSFET Device

## PACKAGE OUTLINE



All dimensions are in inches